



SANYO Semiconductors
DATA SHEET

2SC6065

NPN Triple Diffused Planar Silicon Transistor
Switching Regulator Applications

Features

- High breakdown voltage.
- High-speed switching.
- Wide ASO.
- Adoption of MBIT process.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		500	V
Collector-to-Emitter Voltage	V _{CEO}		400	V
Emitter-to-Base Voltage	V _{EBO}		8	V
Collector Current	I _C		1.5	A
Collector Current (Pulse)	I _{CP}	PW≤300μs, duty cycle≤10%	3	A
Base Current	I _B		0.7	A
Collector Dissipation	P _C		0.9	W
Junction Temperature	T _J		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CBO}	V _{CB} =400V, I _E =0A			10	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V, I _C =0A			10	μA
DC Current Gain	h _{FE1}	V _{CE} =5V, I _C =0.1A	20		50	
	h _{FE2}	V _{CE} =5V, I _C =0.7A	10			
	h _{FE3}	V _{CE} =5V, I _C =1mA	10			

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80906 / 12006CB MS IM TB-00001637 No.8561-1/4

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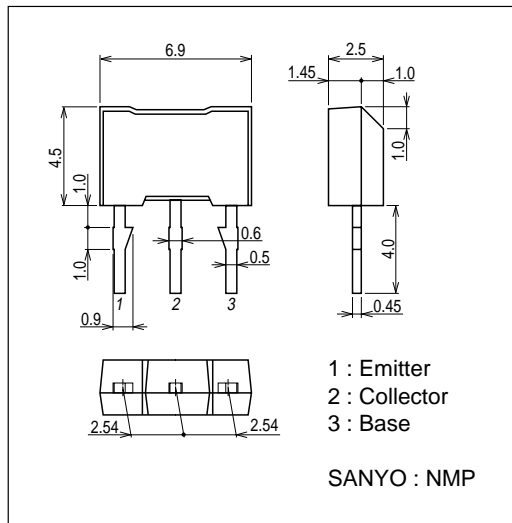
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=0.1A$		20		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		10		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=0.7A, I_B=0.14A$			0.8	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=0.7A, I_B=0.14A$			1.5	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0A$	500			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	400			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0A$	8			V
Turn-ON Time	t_{on}	$I_C=1A, I_{B1}=0.2A, I_{B2}=-0.4A, R_L=200\Omega, V_{CC}=200V$			0.5	μs
Storage Time	t_{stg}	$I_C=1A, I_{B1}=0.2A, I_{B2}=-0.4A, R_L=200\Omega, V_{CC}=200V$			2.5	μs
Fall Time	t_f	$I_C=1A, I_{B1}=0.2A, I_{B2}=-0.4A, R_L=200\Omega, V_{CC}=200V$			0.25	μs

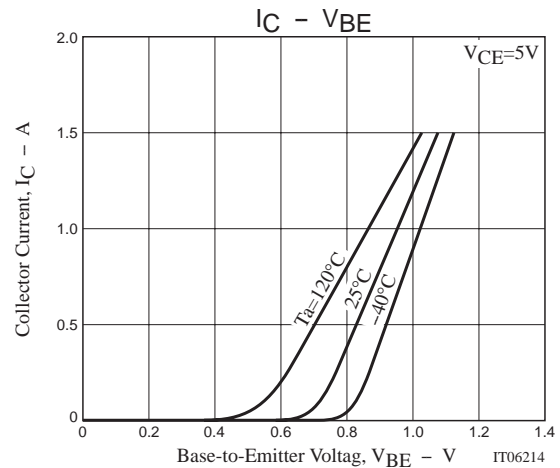
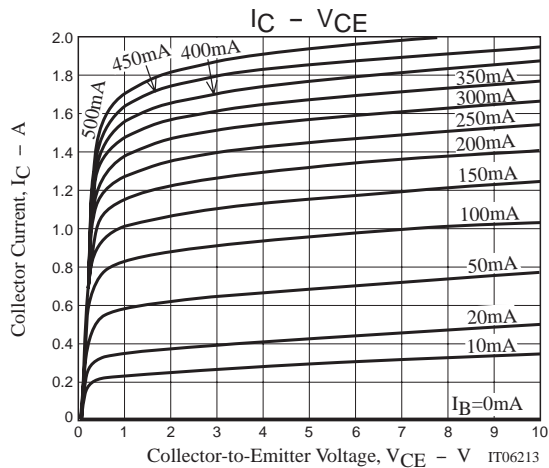
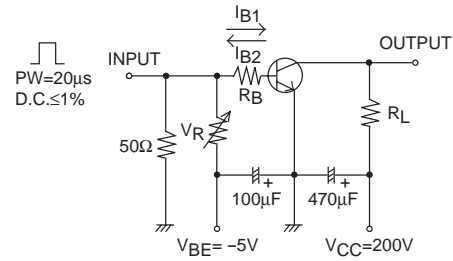
Package Dimensions

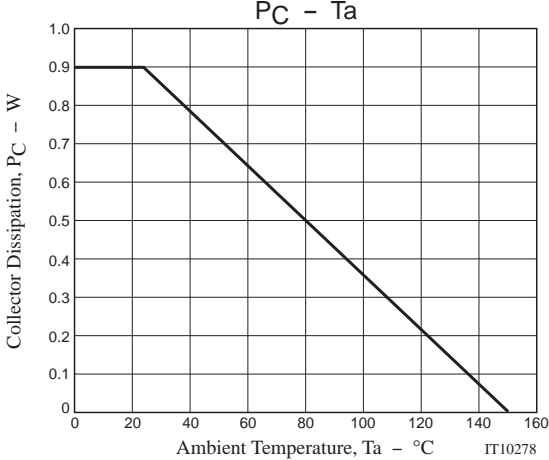
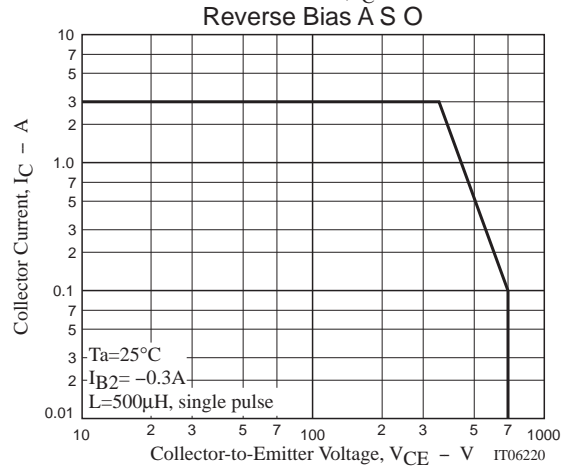
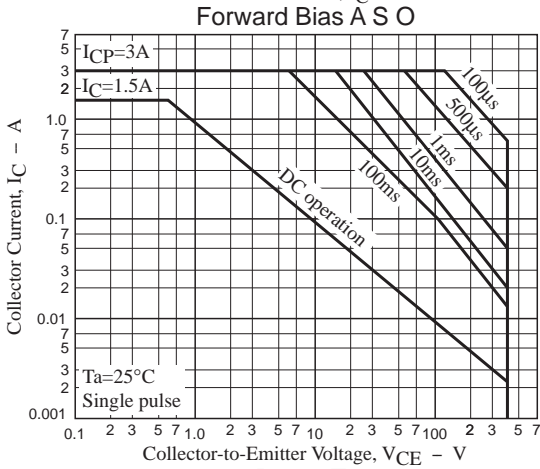
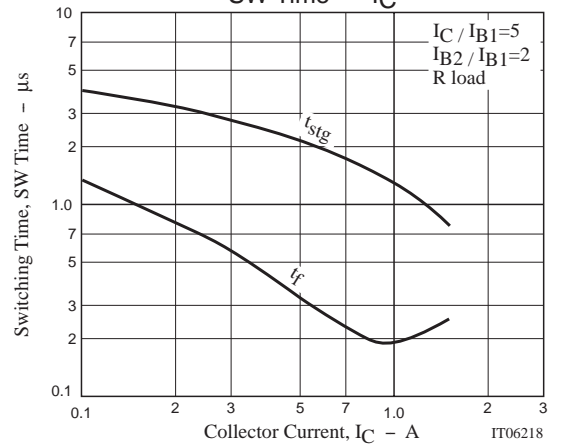
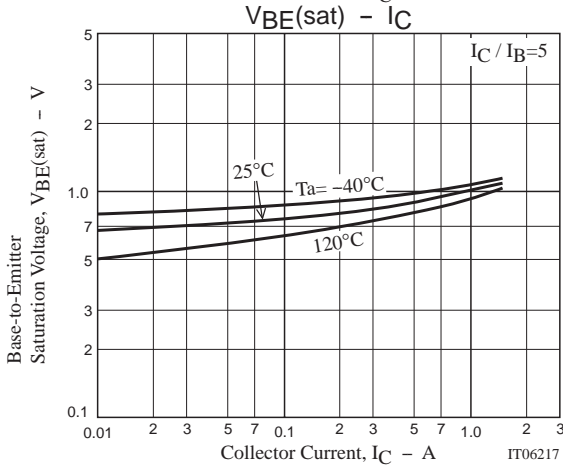
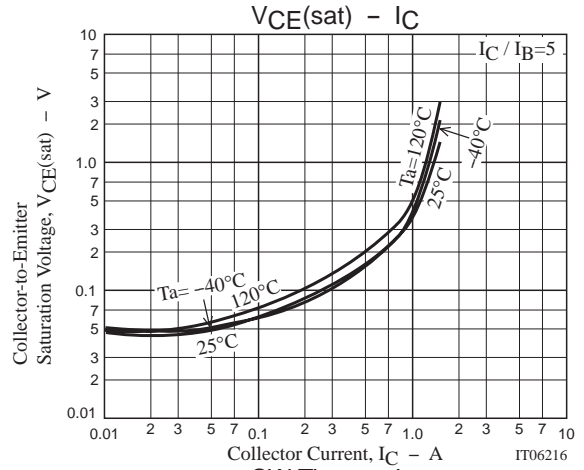
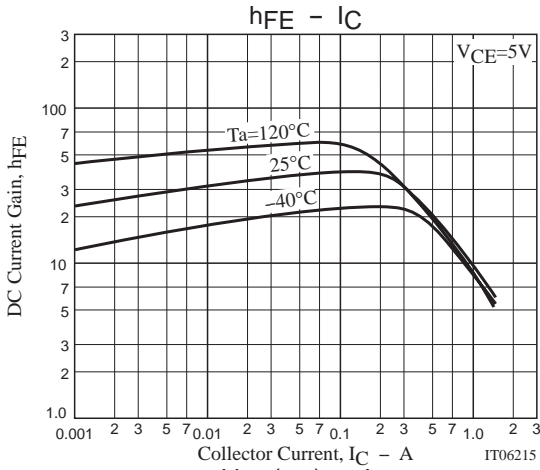
unit : mm

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Switching Time Test Circuit





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